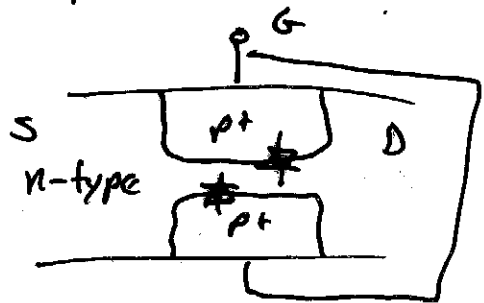
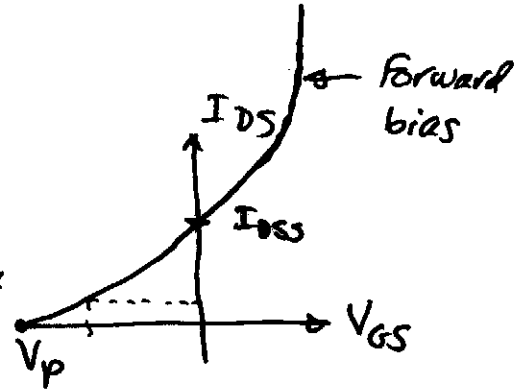
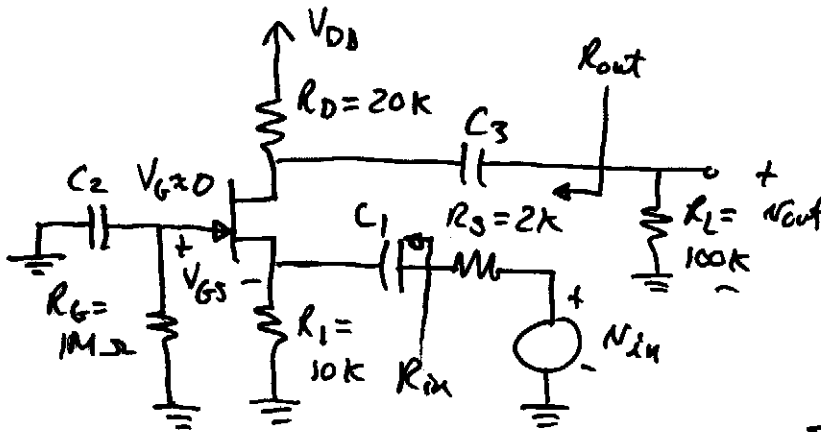


Common Gate JFET Amplifier



DC conditions:

$I_{DS} = 1\text{mA}$, $I_{DSS} = 5\text{mA}$

$V_p = -2\text{V}$, $\lambda = 0 \Rightarrow r_o = \infty$

1.) Small-signal model parameters

$g_m = \sqrt{2I_{DS} K_n (1 + \lambda V_{DS})}$

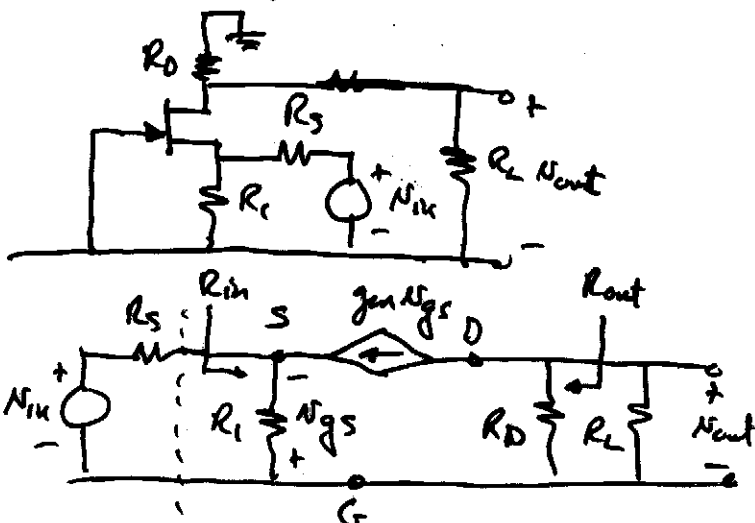
$K_n(\text{JFET}) = \frac{3I_{DSS}}{2|V_p|^2}$

$g_m = \frac{2}{|V_p|} \sqrt{I_{DSS} I_{DS}}$

$I_{DS} = I_{DSS} \left(1 - \frac{V_{GS}}{V_p}\right)^2$

$= \frac{2}{2} \sqrt{5 \cdot 1} \text{ mS} = 2.236 \text{ mS}$ $r_o = \infty$

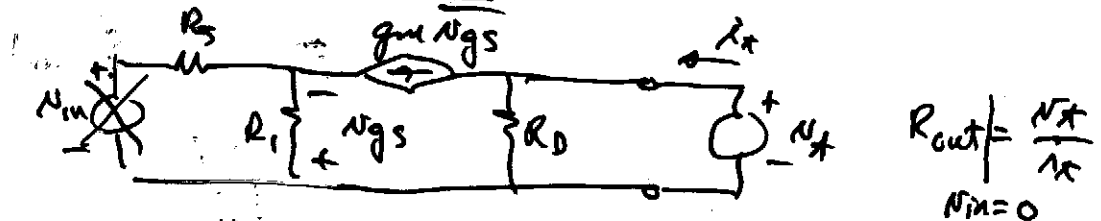
2.) Small-signal model



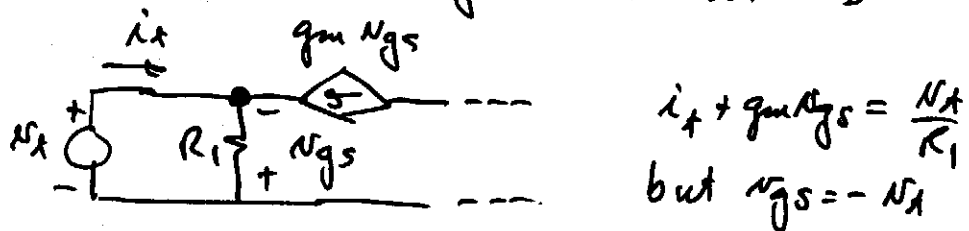
CG - JFET Amplifier - Cont'd

3.) SS Analysis -

$$R_{out} = R_D = \underline{20K}$$



$$v_{in} = 0 \rightarrow v_{gs} = 0 \rightarrow R_{out} = R_D$$



$$\therefore i_x = \frac{v_x}{R_1} + gm v_x = v_x \left(gm + \frac{1}{R_1} \right)$$

$$R_{in} = \frac{1}{gm + \frac{1}{R_1}} = \underline{\underline{428 \Omega}}$$

$$\begin{aligned} \frac{v_{out}}{v_{in}} &= \left(\frac{v_{out}}{v_{gs}} \right) \left(\frac{v_{gs}}{v_{in}} \right) = \left(-gm R_D \parallel R_L \right) \left(\frac{-R_1}{R_1 + R_S} \right) \\ &= \underline{\underline{31.06 V/V}} \end{aligned}$$